修订记录

A	2022.4.7		JSCJ-DTC123JKA+JSCJ-DTA123JKA+LRC-LMUN5335DW1T1G		

Rev.A Apr.-2022

描述

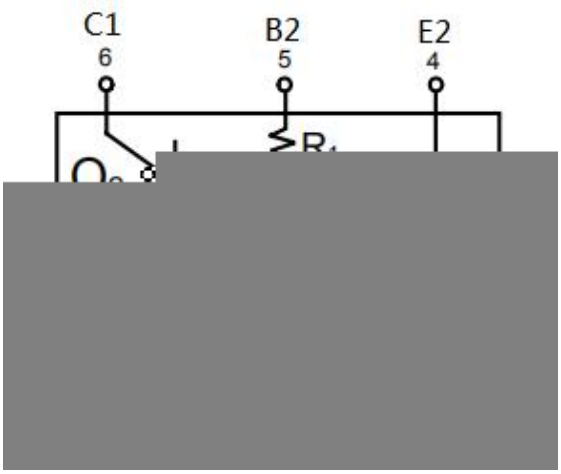
silicon NPN and PNP transistor in a SOT-363 Plastic Package

特征

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process, HF Product.

用途

Switching applications, interface circuit and driver circuit applications.



放大及印章代码

Marking	H335

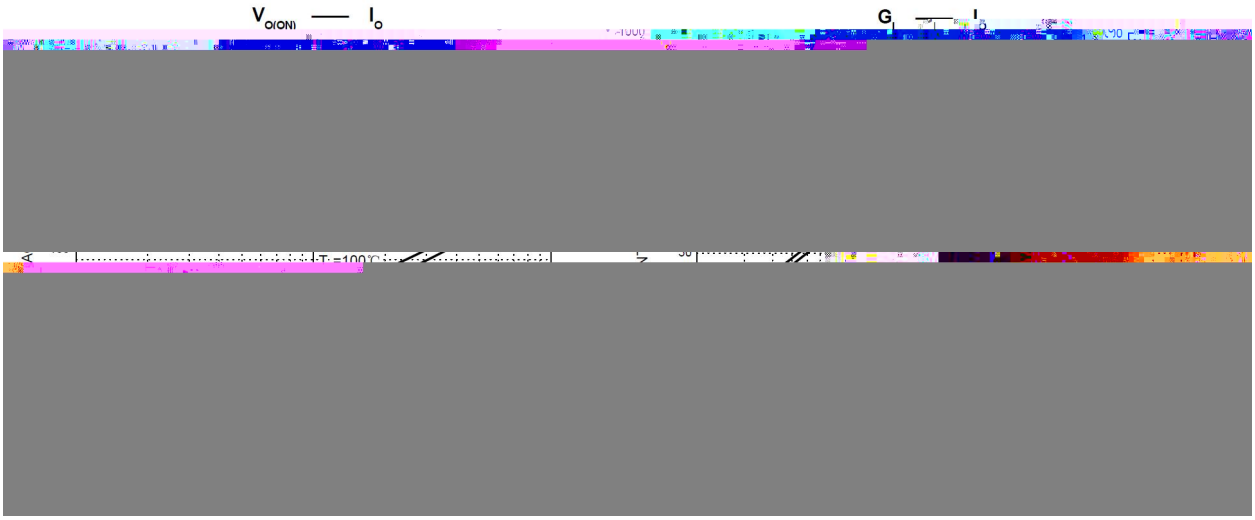
Parameter	Symbol	Rating	Unit
Supply Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	12	V
		-5	V
Output Current	I_O	100	mA
Collector Dissipation	P_C	187	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55～150	

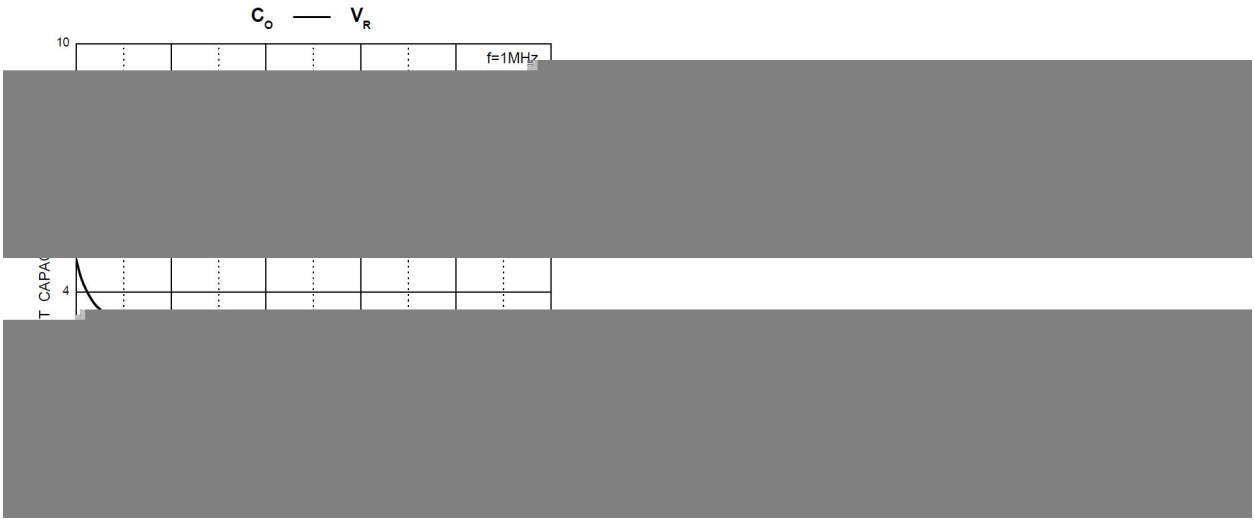
Parameter Symbol

Parameter	Symbol	Rating	Unit
Supply Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	-12	V
		5	V
	I_O	-100	mA
er Dissi		ضذ	

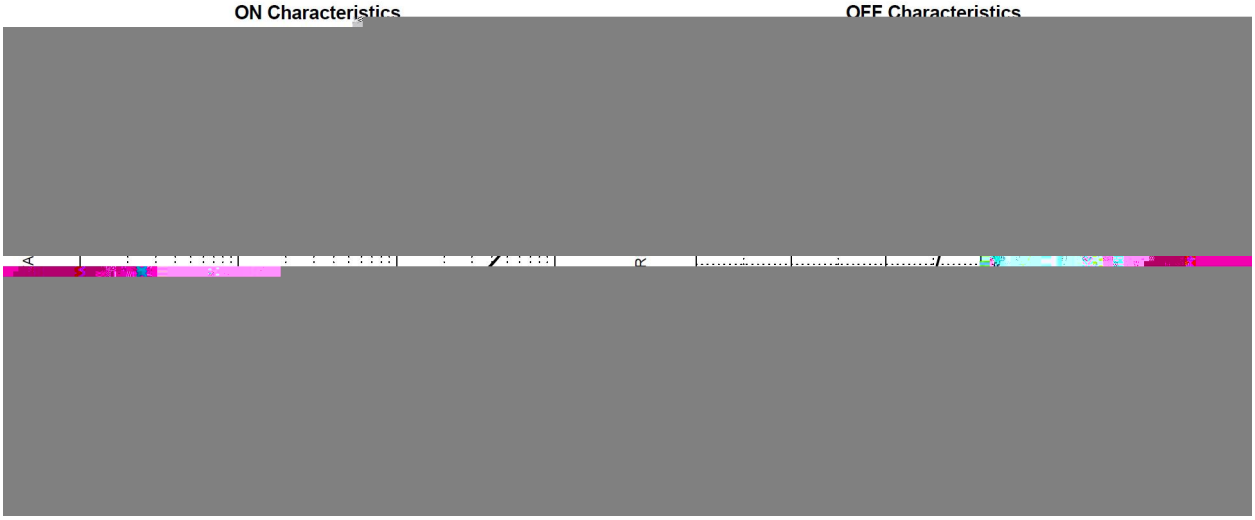
电参数曲线图

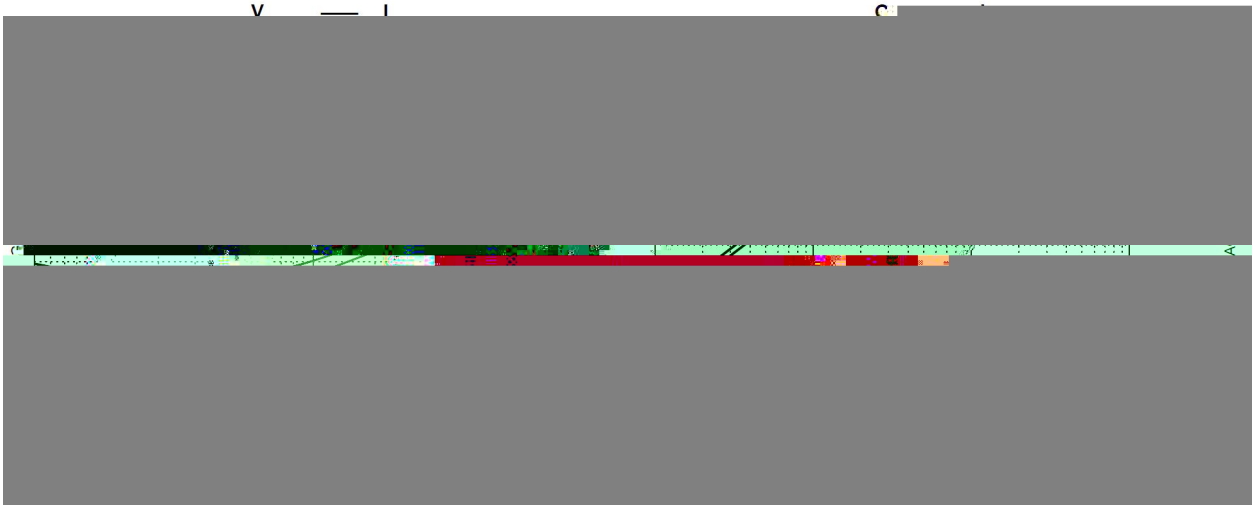
ON Characteristics
OFF Characteristics

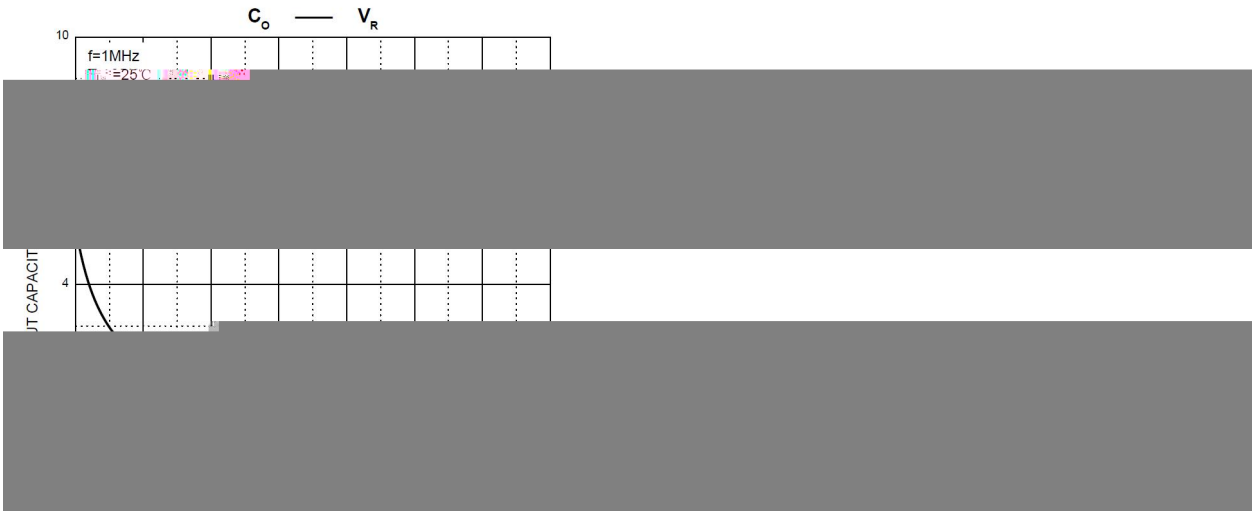

$V_{O(ON)}$ —— I_O
G —— I
T=100℃


C_O —— V_R
f=1MHz

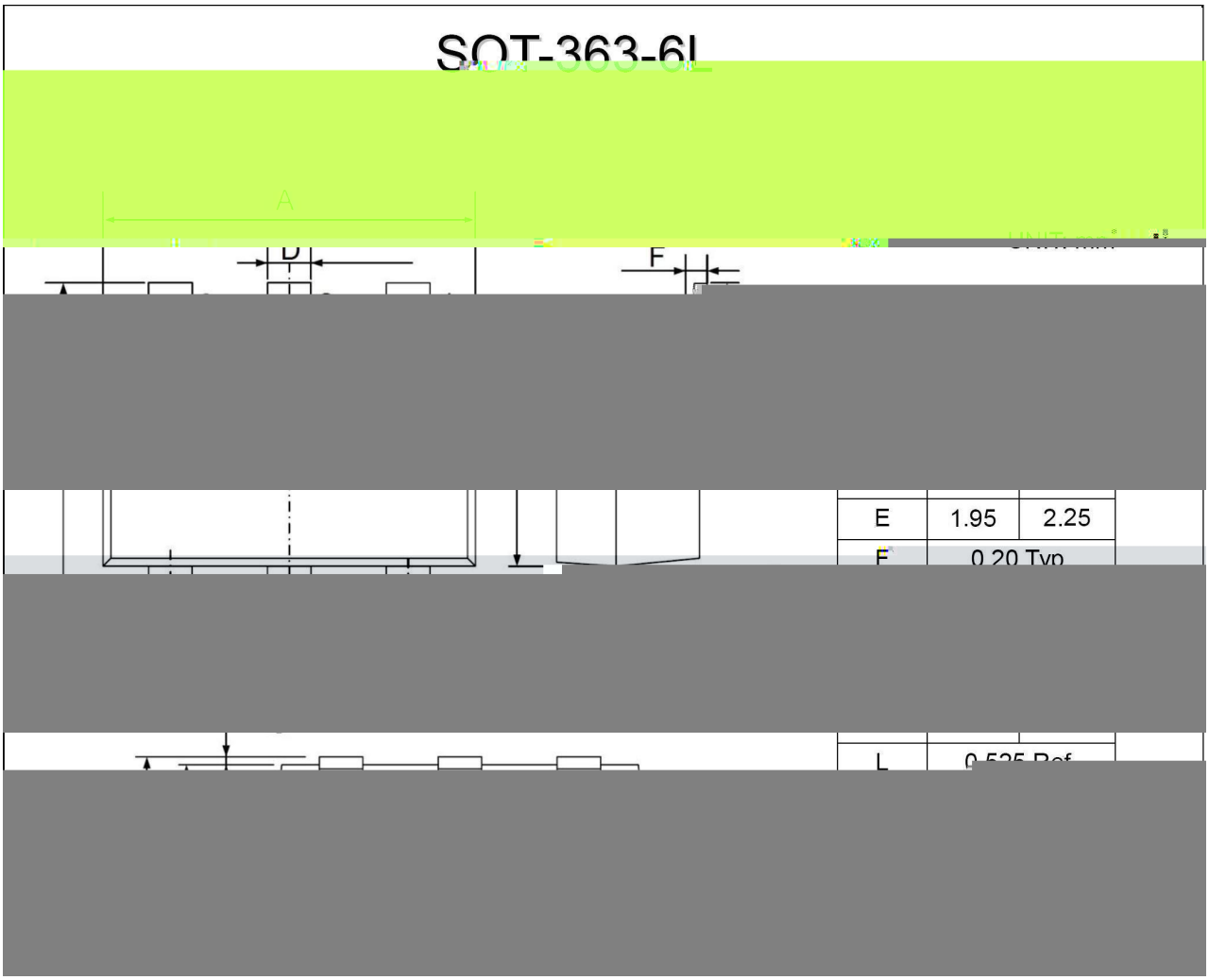
电参数曲线图


ON Characteristics
OFF Characteristics




C_O —— V_R
10
f=1MHz
=25°C
4

外形尺寸图



回流焊温度曲线图 无铅 T mp ratur Pr fil f r IR R fl w S l rin (Pb-Fr)

				Note:
1	150 180	60 90sec;		1.Preheating:150~180 , Time:60~90sec.
2	245 5	5 0.5sec;		